

Silicon PNP Power Transistors

2SA1094

DESCRIPTION

- With MT-200 package
- Complement to type 2SC2564

APPLICATIONS

- For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

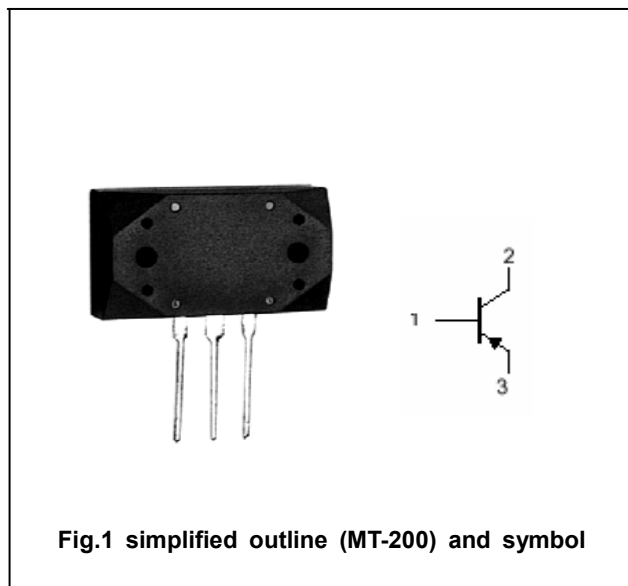


Fig.1 simplified outline (MT-200) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-140	V
V _{CEO}	Collector-emitter voltage	Open base	-140	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-12	A
I _B	Base current		-1.2	A
P _C	Collector power dissipation	T _C =25°C	120	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-0.1A; I_B=0$	-140			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-0.01A; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A; I_B=-0.5A$			-2.0	V
V_{BE}	Base-emitter on voltage	$I_C=-5A; V_{CE}=-5V$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-140V; I_E=0$			-50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-50	μA
h_{FE-1}	DC current gain	$I_C=-1A; V_{CE}=-5V$	55		240	
h_{FE-2}	DC current gain	$I_C=-5A; V_{CE}=-5V$	30			
C_{ob}	Output capacitance	$I_E=0; V_{CB}=-10V; f=1MHz$		220		pF
f_T	Transition frequency	$I_C=-1A; V_{CE}=-10V$		70		MHz

◆ h_{FE-1} classifications

R	O	Y
55-110	80-160	120-240

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PACKAGE OUTLINE

